

SUBSTRATE PROCESSING APPARATUS, PLASMA GENERATION APPARATUS,
METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING
SEMICONDUCTOR DEVICE, AND RECORDING MEDIUM

ABSTRACT

There is provided a technique that includes: a process chamber configured to process a plurality of substrates; and a plasma generator configured to generate plasma in the process chamber, the plasma generator including a first electrode part configured to extend from a lower side to an intermediate side of the process chamber, and a second electrode part configured to extend from an upper side to the intermediate side of the process chamber.

Fig. 6A